
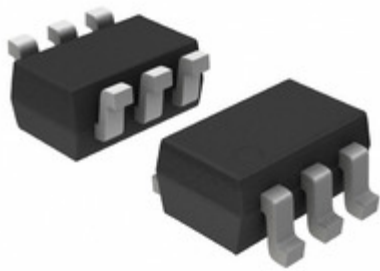

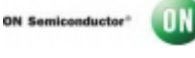



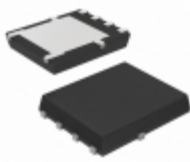
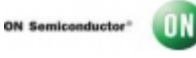

	<h2 style="color: red;">NVJS4405NT1G</h2>
	<p>Hersteller-Teilenummer: NVJS4405NT1G</p> <hr/> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <hr/> <p>Teil der Beschreibung: MOSFET N-CH 25V 1.2A SC88</p> <hr/> <p>Datenblätter:  NVJS4405NT1G.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, 3000 pcs Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	NVJS4405NT1G
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 25V 1.2A SC88
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	3000 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	6-TSSOP, SC-88, SOT-363
Supplier Device-Gehäuse	SC-88/SC70-6/SOT-363
Verlustleistung (max)	630mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	25V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	1A (Ta)
Rds On (Max) @ Id, Vgs	350 mOhm @ 600mA, 4.5V
VGS (th) (Max) @ Id	1.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	1.5nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	60pF @ 10V
Verpackung	Tape & Reel (TR)

NVJS4405NT1G ist neu im Original, Suche NVJS4405NT1G Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie NVJS4405NT1G AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage NVJS4405NT1G: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>NVJD5121NT1G AMI Semiconductor / ON Semiconductor MOSFET 2N-CH 60V 0.295A SC88</p>	 <p>NVJD4158CT1G AMI Semiconductor / ON Semiconductor NVJD4158CT1G ON</p>	 <p>BUK9518-55A,127 Nexperia MOSFET N-CH 55V 61A TO220AB</p>	 <p>NVJS4151PT1G AMI Semiconductor / ON Semiconductor MOSFET P-CH 20V 3.2A SC88</p>
 <p>DMP34M4SPS-13 Diodes Incorporated MOSFET BVDSS: 25V 30V POWERDI506</p>	 <p>NVMFS5C426NLT1G AMI Semiconductor / ON Semiconductor 40V 1.2 MOHM T6 S08FL SIN</p>	 <p>NVJD4152PT1G AMI Semiconductor / ON Semiconductor NVJD4152PT1G ON</p>	 <p>IXFT58N20Q TRL IXYS Corporation MOSFET N-CH 200V 58A TO268</p>

heiße Teile

Mehr

08055C105KAT2A	111RLA120	23Z128SM-T	ADR5041BRTZ	ADUM1100BR
BCM4306KFB-P30	BCR133TE6327	BCR5KM-12LA-1	BQ24266RGER	BSV236SPL6327
C20T10Q-11A	CDP68HC68T1M2	EMK107BJ474KAHT	EPCQ256S116N	FA53SA50
FMMT634QTA	GP1S23J0000F	GRM0336T1E6R8DD01D	GRM31A7U3A121JW31D	HTT170N600KOB
IPS6021R	IRF6619TRPBF.	IRFB4233PBF	LM4040BIM3X-4.1	LMH6715MAX
LQW15AN72NG00D	MAX3088ESA+T	MAX488EPA	MCH3444-TL-E	MDK950-22N1W
MTC160A1600V	NVJD4152PT1G	NVJD4158CT1G	NVJD4401NT1G	NVJD5121NT1G
NVJS3151PT1G	NVJS4151PT1G	P4SMA120A	PBC13900DMR2	R0577YS08C
S9S12GN48VLH	SDU03N04A	SI7540DP-T1-E3	SIA443DJ-T1-GE3	SKM300GB124DH4E
SXA-389BZ	TL082IPT	TPS77433DGKR	UPD720102F1-CA7-A	ZL30143GGG2

Contact us: Info@Y-IC.com

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